

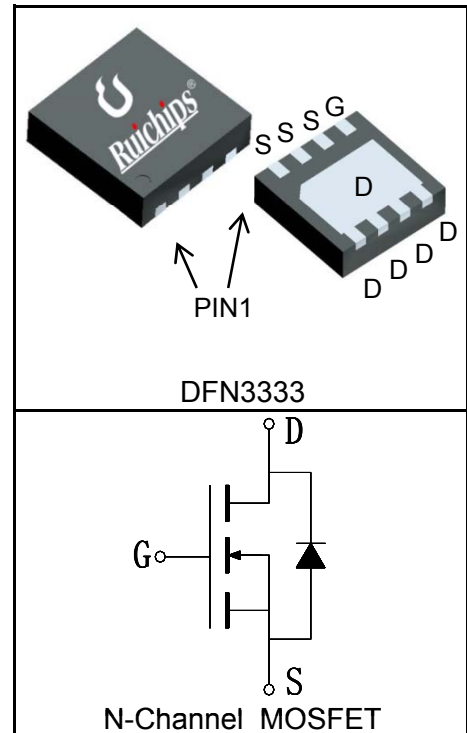
Features

- 30V/40A,
- $R_{DS(ON)} = 5m\Omega(Typ.)@V_{GS}=10V$
- $R_{DS(ON)} = 6.5m\Omega(Typ.)@V_{GS}=4.5V$
- Super High Dense Cell Design
- Fast Switching Speed
- Low gate Charge
- 100% avalanche tested
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- Switching Application Systems
- On Board power for server
- Synchronous rectification

Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _C =25°C	40	A
Mounted on Large Heat Sink				
I _{DP} ^①	300μs Pulse Drain Current Tested	T _C =25°C	160	A
I _D ^②	Continuous Drain Current@T _C (V _{GS} =10V)	T _C =25°C	40	A
		T _C =100°C	25	
	Continuous Drain Current@T _A (V _{GS} =10V) ^③	T _A =25°C	13	
		T _A =70°C	11	
P _D	Maximum Power Dissipation@T _C	T _C =25°C	31	W
		T _C =100°C	13	
	Maximum Power Dissipation@T _A ^③	T _A =25°C	3.5	
		T _A =70°C	2.3	

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	4	°C/W
$R_{\theta JA}^{(3)}$	Thermal Resistance-Junction to Ambient	35	°C/W
Drain-Source Avalanche Ratings			
$E_{AS}^{(4)}$	Avalanche Energy, Single Pulsed	90	mJ

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU3040M3			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V			1	μA
			T _J =125°C			
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.9		1.8	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =25A		5	6.5	mΩ
		V _{GS} =4.5V, I _{DS} =20A		6.5	8	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =25A, V _{GS} =0V			1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =25A, dI _{SD} /dt=100A/μs		17		ns
Q _{rr}	Reverse Recovery Charge			9		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		1		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz		680		pF
C _{oss}	Output Capacitance			175		
C _{rss}	Reverse Transfer Capacitance			80		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, I _{DS} =25A, V _{GEN} =10V, R _G =2.4Ω		6		ns
t _r	Turn-on Rise Time			10		
t _{d(OFF)}	Turn-off Delay Time			16		
t _f	Turn-off Fall Time			4		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =24V, V _{GS} =10V, I _{DS} =25A		15		nC
Q _{gs}	Gate-Source Charge			3.8		
Q _{gd}	Gate-Drain Charge			5.5		

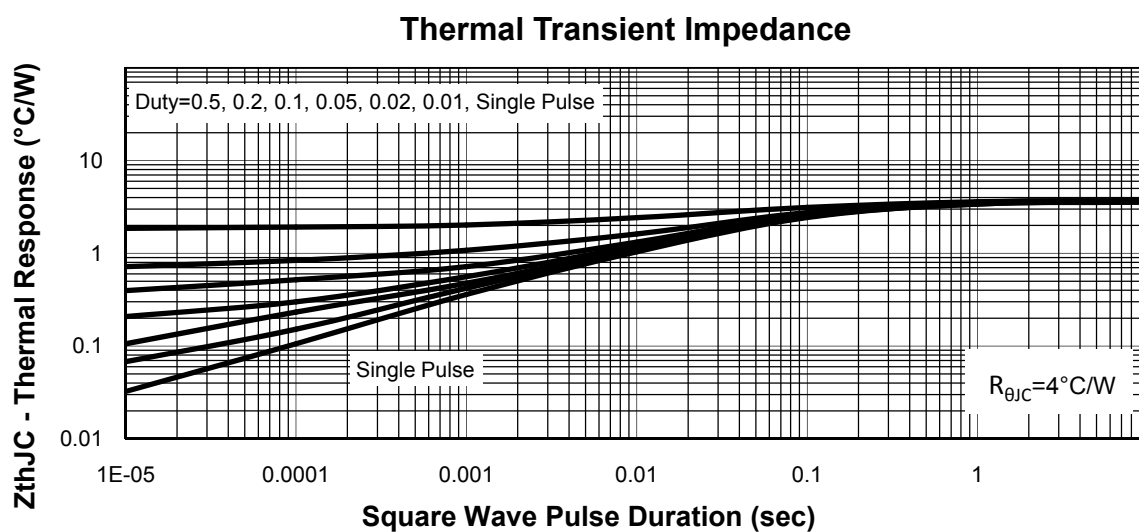
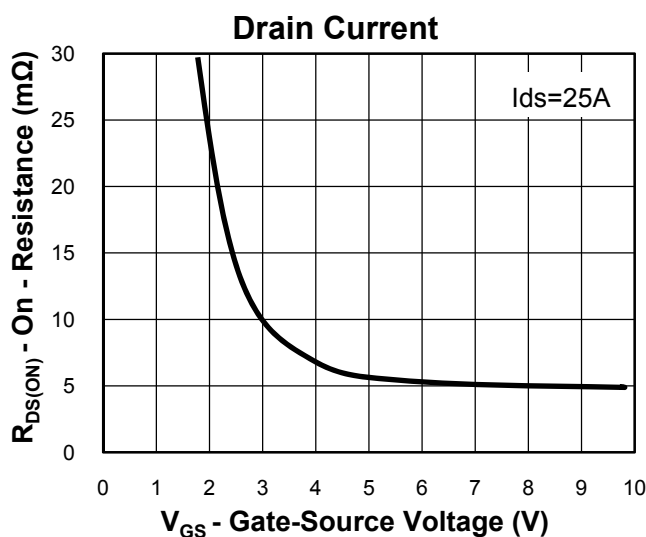
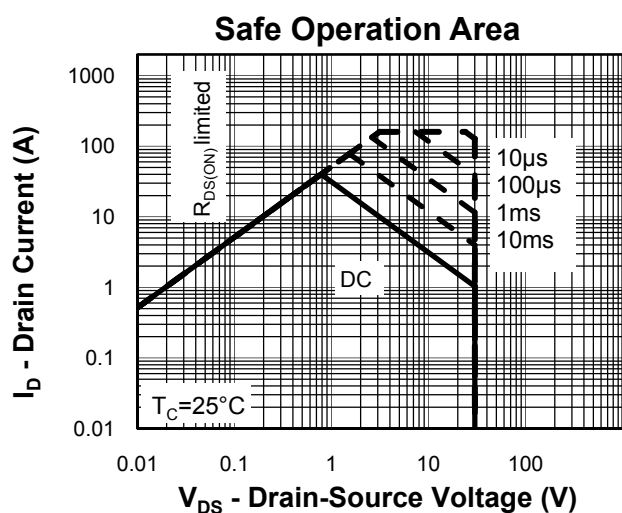
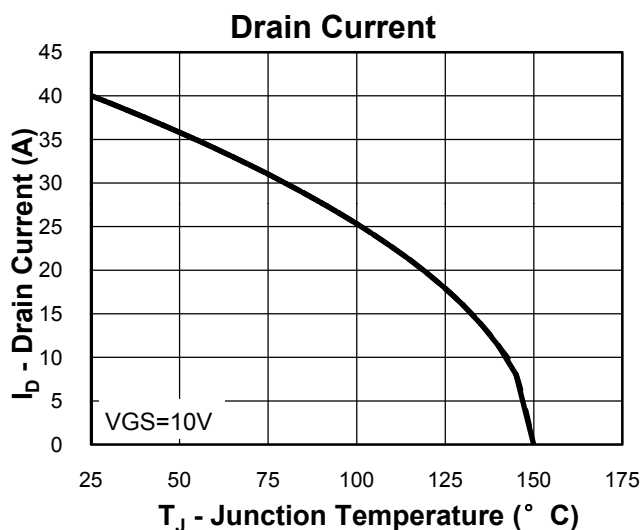
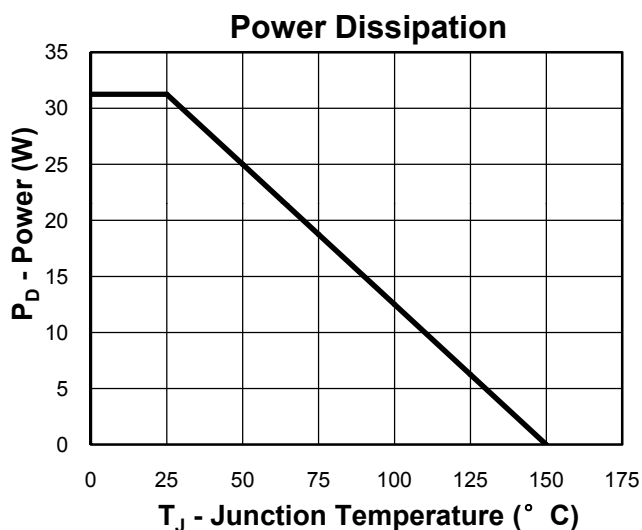
Notes:

- ①Pulse width limited by safe operating area.
- ②Calculated continuous current based on maximum allowable junction temperature.
- ③When mounted on 1 inch square copper board, $t \leq 10\text{sec}$.
- ④Limited by $T_{J\max}$, $I_{AS} = 19\text{A}$, $V_{DD} = 24\text{V}$, $R_G = 50\Omega$, Starting $T_J = 25^\circ\text{C}$.
- ⑤Pulse test;Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- ⑥Guaranteed by design, not subject to production testing.

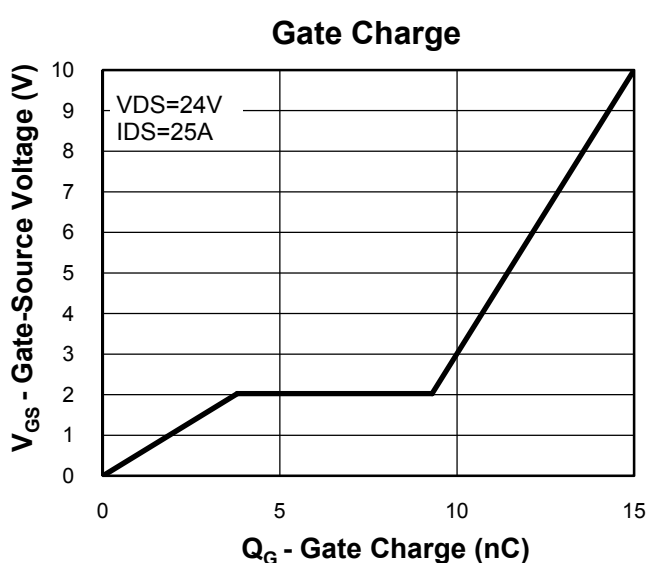
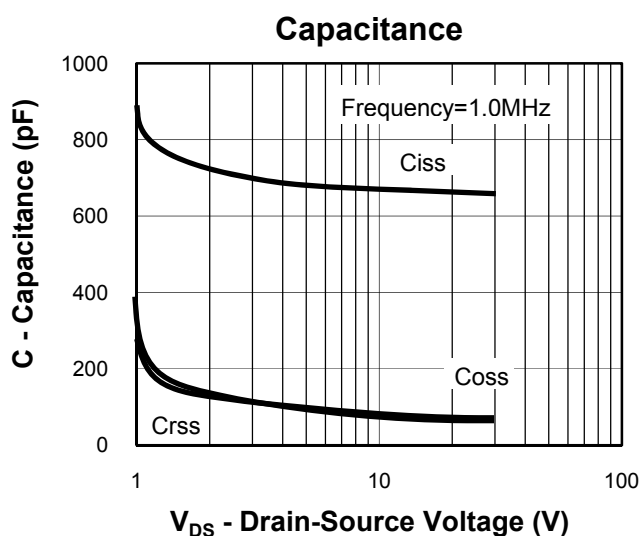
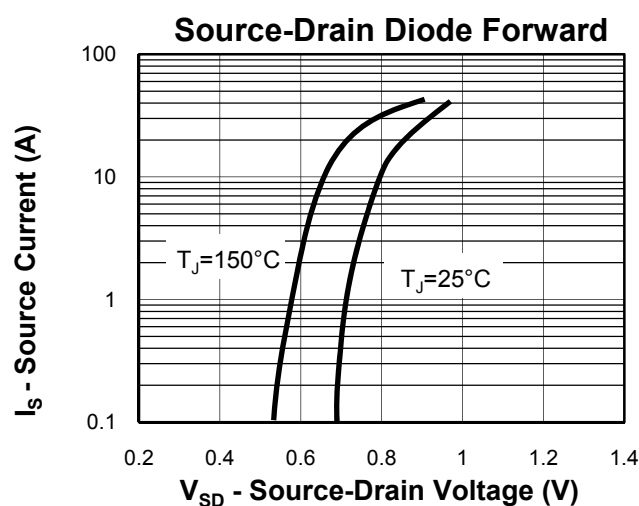
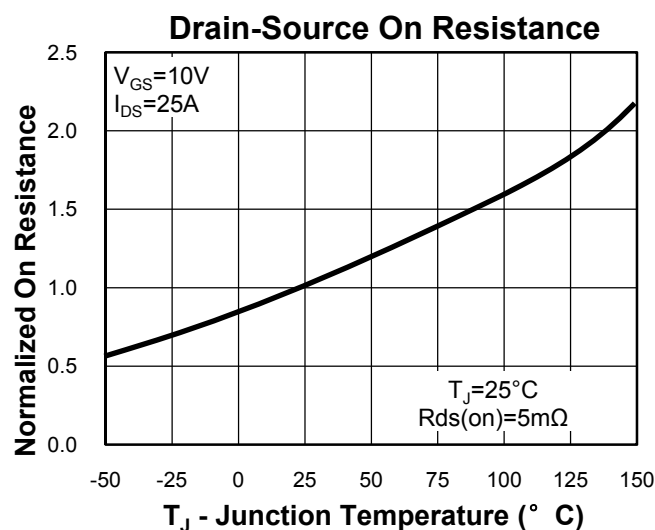
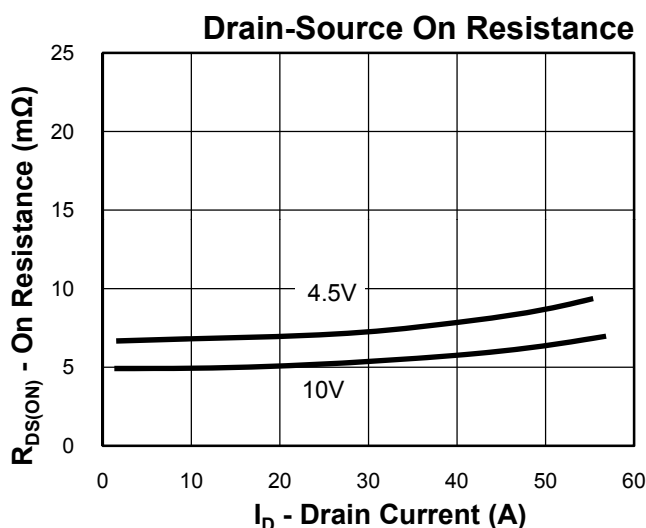
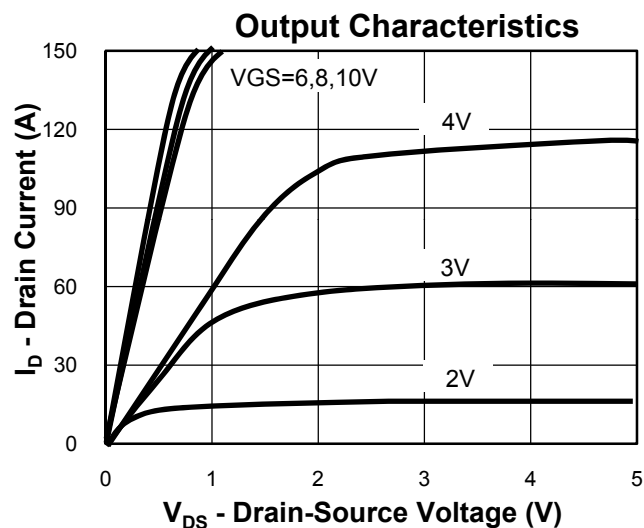
Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU3040M3	RU3040	DFN3333	Tape&Reel	5000	13"	12mm

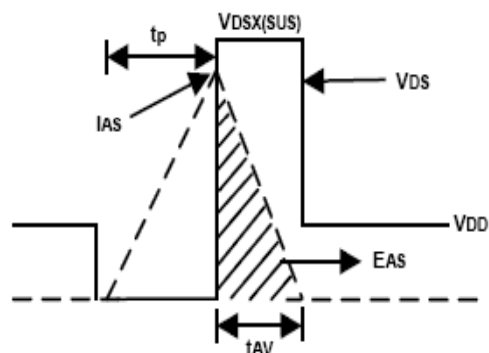
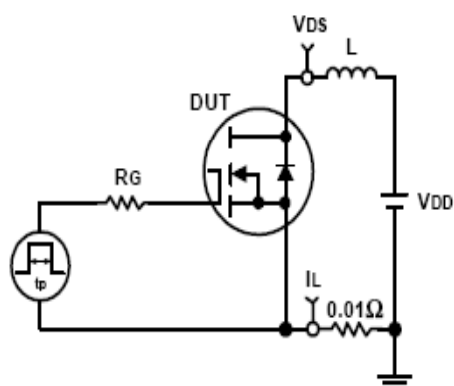
Typical Characteristics



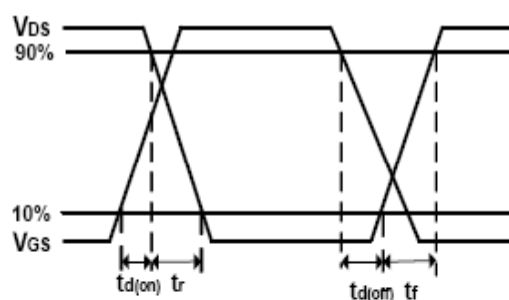
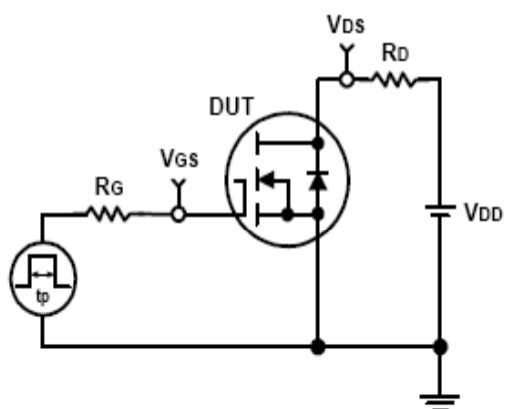
Typical Characteristics



Avalanche Test Circuit and Waveforms

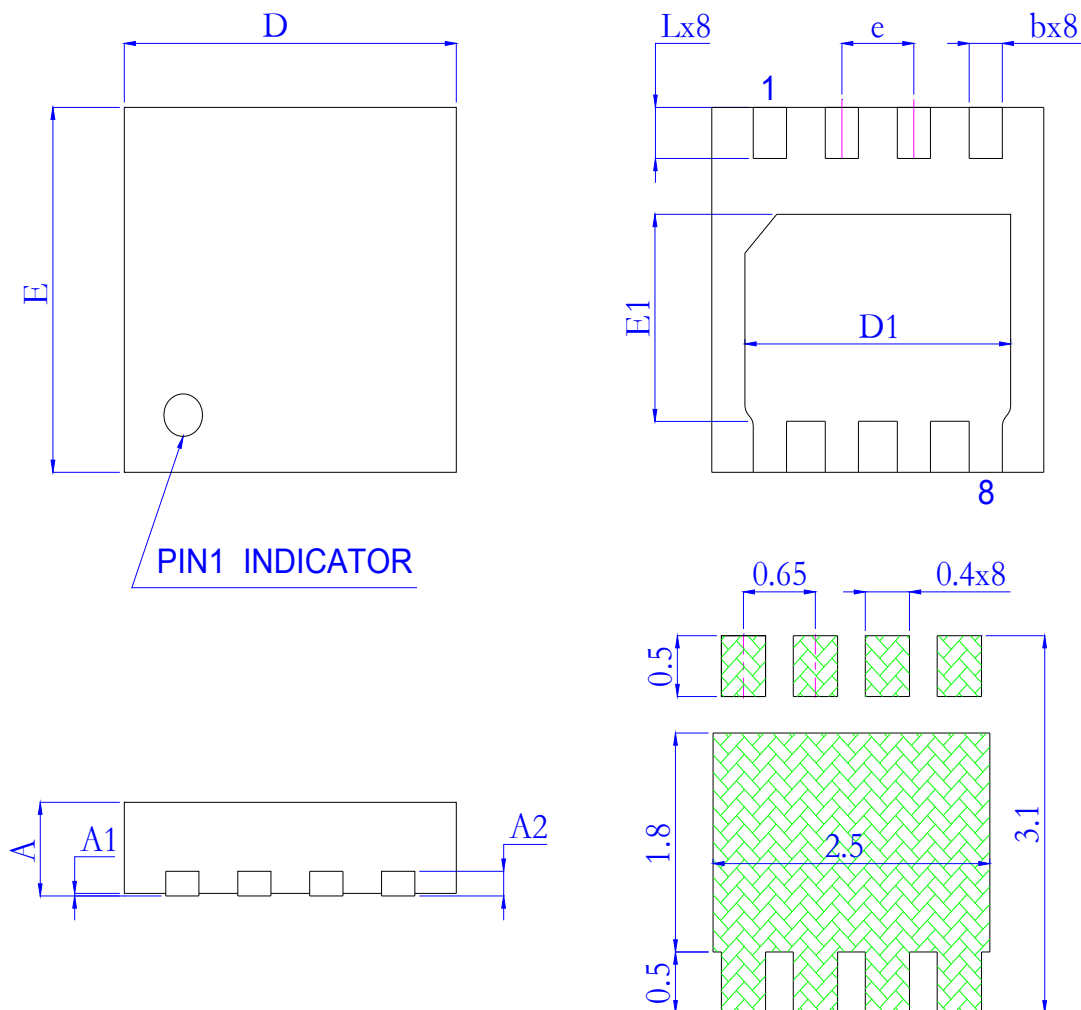


Switching Time Test Circuit and Waveforms



Package Information

DFN3333



Land Pattern
(Only for Reference)

SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.750	0.800	0.028	0.030	0.031
A1	0.000	0.020	0.050	0.000	0.001	0.002
A2	0.203 REF.			0.008 REF.		
b	0.250	0.300	0.350	0.010	0.012	0.014
D	3.000	3.150	3.300	0.118	0.124	0.130
D1	2.350	2.400	2.450	0.093	0.094	0.096
E	3.000	3.150	3.300	0.118	0.124	0.130
E1	1.650	1.700	1.750	0.065	0.067	0.069
e	0.650BSC			0.026BSC		
L	0.370	0.420	0.470	0.015	0.017	0.019

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